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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	110592
Number of I/O	154
Number of Gates	600000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/m1a3p600l-pq208i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Microsemi

Flash*Freeze Technology and Low Power Modes

Flash Families Support the Flash*Freeze Feature

The low power flash FPGAs listed in Table 2-1 support the Flash*Freeze feature and the functions described in this document.

Table 2-1 • Flash-Based FPGAs

Series	Family [*]	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L

Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 2-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 2-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio.*

Using Sleep and Shutdown Modes in the System

Depending on the power supply and the components used in an application, there are many ways to power on or off the power supplies connected to the device. For example, Figure 2-6 shows how a microprocessor can be used to control a power FET. Microsemi recommends that power FETs with low resistance be used to perform the switching action.

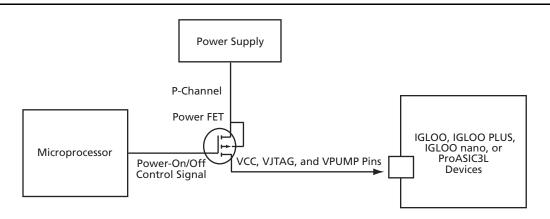


Figure 2-6 • Controlling Power-On/-Off State Using Microprocessor and Power FET

Figure 2-7 shows how a microprocessor can be used with a voltage regulator's shutdown pin to turn on or off the power supplies connected to the device.

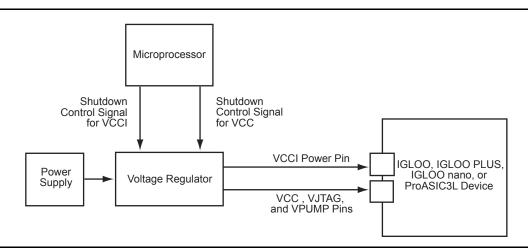


Figure 2-7 • Controlling Power-On/-Off State Using Microprocessor and Voltage Regulator

Power-Up/-Down Behavior

By design, all IGLOO, IGLOO nano, IGLOO PLUS, ProASIC3L, and RT ProASIC3 I/Os are in tristate mode before device power-up. The I/Os remain tristated until the last voltage supply (V_{CC} or V_{CCI}) is powered to its activation level. After the last supply reaches its functional level, the outputs exit the tristate mode and drive the logic at the input of the output buffer. The behavior of user I/Os is independent of the V_{CC} and V_{CCI} sequence or the state of other voltage supplies of the FPGA (V_{PUMP} and V_{JTAG}). During power-down, device I/Os become tristated once the first power supply (V_{CC} or V_{CCI}) drops below its deactivation voltage level. The I/O behavior during power-down is also independent of voltage supply sequencing.

Figure 2-8 on page 34 shows a timing diagram when the V_{CC} power supply crosses the activation and deactivation trip points in a typical application when the V_{CC} power supply ramp-rate is 100 μ s (ramping from 0 V to 1.5 V in this example). This is the timing diagram for the FPGA entering and exiting Sleep mode, as this function is dependent on powering V_{CC} down or up. Depending on the ramp-rate of the

Spine Access

The physical location of each spine is identified by the letter T (top) or B (bottom) and an accompanying number (T*n* or B*n*). The number *n* indicates the horizontal location of the spine; 1 refers to the first spine on the left side of the die. Since there are six chip spines in each spine tree, there are up to six spines available for each combination of T (or B) and *n* (for example, six T1 spines). Similarly, there are three quadrant spines available for each combination of T (or B) and *n* (for example, four T1 spines), as shown in Figure 3-7.

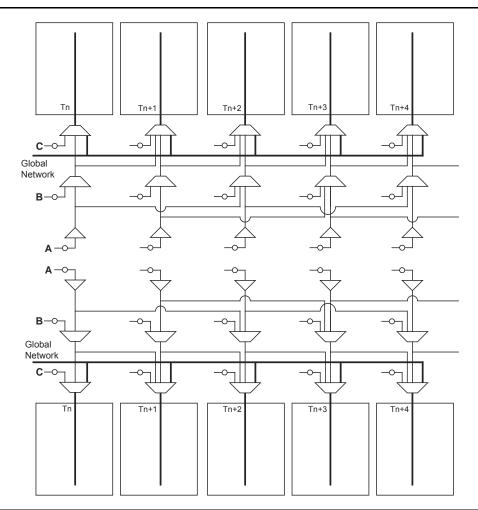


Figure 3-7 • Chip Global Aggregation

A spine is also called a local clock network, and is accessed by the dedicated global MUX architecture. These MUXes define how a particular spine is driven. Refer to Figure 3-8 on page 60 for the global MUX architecture. The MUXes for each chip global spine are located in the middle of the die. Access to the top and bottom chip global spine is available from the middle of the die. There is no control dependency between the top and bottom spines. If a top spine, T1, of a chip global network is assigned to a net, B1 is not wasted and can be used by the global clock network. The signal assigned only to the top or bottom spine cannot access the middle two rows of the architecture. However, if a spine is using the top and bottom at the same time (T1 and B1, for instance), the previous restriction is lifted.

The MUXes for each quadrant global spine are located in the north and south sides of the die. Access to the top and bottom quadrant global spines is available from the north and south sides of the die. Since the MUXes for quadrant spines are located in the north and south sides of the die, you should not try to drive T1 and B1 quadrant spines from the same signal.



Global Resources in Low Power Flash Devices

Global Macro and Placement Selections

Low power flash devices provide the flexibility of choosing one of the three global input pad locations available to connect to a global / quadrant global network. For 60K gate devices and above, if the single-ended I/O standard is chosen, there is flexibility to choose one of the global input pads (the first, second, and fourth input). Once chosen, the other I/O locations are used as regular I/Os. If the differential I/O standard is chosen, the first and second inputs are considered as paired, and the third input is paired with a regular I/O. The user then has the choice of selecting one of the two sets to be used as the global input source. There is also the option to allow an internal clock signal to feed the global network. A multiplexer tree selects the appropriate global input for routing to the desired location. Note that the global I/O pads do not need to feed the global network; they can also be used as regular I/O pads.

Hardwired I/O Clock Source

Hardwired I/O refers to global input pins that are hardwired to the multiplexer tree, which directly accesses the global network. These global input pins have designated pin locations and are indicated with the I/O naming convention Gmn (m refers to any one of the positions where the global buffers is available, and n refers to any one of the three global input MUXes and the pin number of the associated global location, m). Choosing this option provides the benefit of directly connecting to the global buffers, which provides less delay. See Figure 3-11 for an example illustration of the connections, shown in red. If a CLKBUF macro is initiated, the clock input can be placed at one of nine dedicated global input pin locations: GmA0, GmA1, GmA2, GmB0, GmB1, GmB2, GmC0, GmC1, or GmC2. Note that the placement of the global will determine whether you are using chip global or quadrant global. For example, if the CLKBIF is placed in one of the GF pin locations, it will use the chip global network; if the CLKBIF is placed in one of the GA pin locations, it will use the chip global network. This is shown in Figure 3-12 on page 65 and Figure 3-13 on page 65.

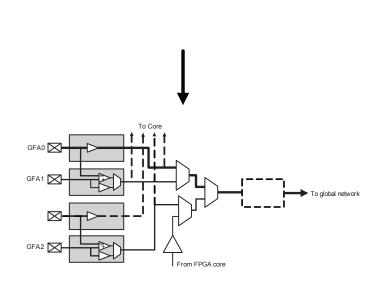


Figure 3-11 • CLKBUF Macro



Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

PLL Macro Signal Descriptions

The PLL macro supports two inputs and up to six outputs. Table 4-3 gives a description of each signal.

Table 4-3 • Input and Output Signals of the PLL Block

Signal	Name	I/O	Description
CLKA	Reference Clock	Input	Reference clock input for PLL core; input clock for primary output clock, GLA
OADIVRST	Reset Signal for the Output Divider A	Input	For Fusion only. OADIVRST can be used when you bypass the PLL core (i.e., OAMUX = 001). The purpose of the OADIVRST signals is to reset the output of the final clock divider to synchronize it with the input to that divider when the PLL is bypassed. The signal is active on a low to high transition. The signal must be low for at least one divider input. If PLL core is used, this signal is "don't care" and the internal circuitry will generate the reset signal for the synchronization purpose.
OADIVHALF	Output A Division by Half	Input	For Fusion only. Active high. Division by half feature. This feature can only be used when users bypass the PLL core (i.e., OAMUX = 001) and the RC Oscillator (RCOSC) drives the CLKA input. This can be used to divide the 100 MHz RC oscillator by a factor of 1.5, 2.5, 3.5, 4.5 14.5). Refer to Table 4-18 on page 111 for more information.
EXTFB	External Feedback	Input	Allows an external signal to be compared to a reference clock in the PLL core's phase detector.
POWERDOWN	Power Down	Input	Active low input that selects power-down mode and disables the PLL. With the POWERDOWN signal asserted, the PLL core sends 0 V signals on all of the outputs.
GLA	Primary Output	Output	Primary output clock to respective global/quadrant clock networks
GLB	Secondary 1 Output	Output	Secondary 1 output clock to respective global/quadrant clock networks
YB	Core 1 Output	Output	Core 1 output clock to local routing network
GLC	Secondary 2 Output	Output	Secondary 2 output clock to respective global/quadrant clock networks
YC	Core 2 Output	Output	Core 2 output clock to local routing network
LOCK	PLL Lock Indicator	Output	Active high signal indicating that steady-state lock has been achieved between CLKA and the PLL feedback signal

Input Clock

The inputs to the input reference clock (CLKA) of the PLL can come from global input pins, regular I/O pins, or internally from the core. For Fusion families, the input reference clock can also be from the embedded RC oscillator or crystal oscillator.

Global Output Clocks

GLA (Primary), GLB (Secondary 1), and GLC (Secondary 2) are the outputs of Global Multiplexer 1, Global Multiplexer 2, and Global Multiplexer 3, respectively. These signals (GLx) can be used to drive the high-speed global and quadrant networks of the low power flash devices.

A global multiplexer block consists of the input routing for selecting the input signal for the GLx clock and the output multiplexer, as well as delay elements associated with that clock.

Core Output Clocks

YB and YC are known as Core Outputs and can be used to drive internal logic without using global network resources. This is especially helpful when global network resources must be conserved and utilized for other timing-critical paths.



Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

Core Logic Clock Source

Core logic refers to internal routed nets. Internal routed signals access the CCC via the FPGA Core Fabric. Similar to the External I/O option, whenever the clock source comes internally from the core itself, the routed signal is instantiated with a PLLINT macro before connecting to the CCC clock input (see Figure 4-12 for an example illustration of the connections, shown in red).

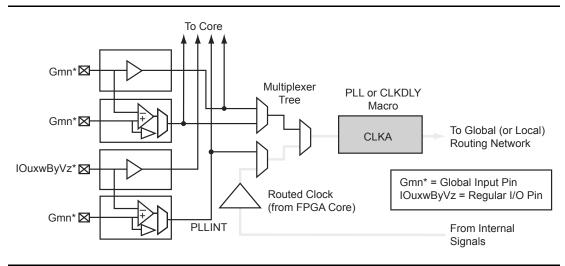


Figure 4-12 • Illustration of Core Logic Usage

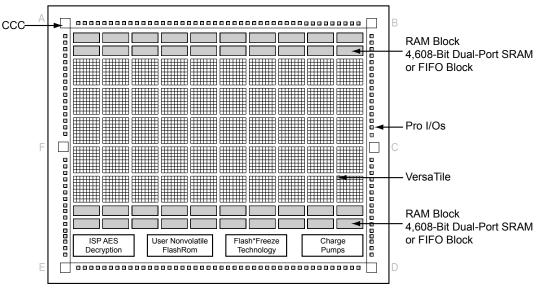
For Fusion devices, the input reference clock can also be from the embedded RC oscillator and crystal oscillator. In this case, the CCC configuration is the same as the hardwired I/O clock source, and users are required to instantiate the RC oscillator or crystal oscillator macro and connect its output to the input reference clock of the CCC block.

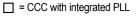
Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

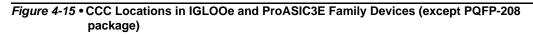
IGLOOe and ProASIC3E CCC Locations

IGLOOe and ProASIC3E devices have six CCCs—one in each of the four corners and one each in the middle of the east and west sides of the device (Figure 4-15).

All six CCCs are integrated with PLLs, except in PQFP-208 package devices. PQFP-208 package devices also have six CCCs, of which two include PLLs and four are simplified CCCs. The CCCs with PLLs are implemented in the middle of the east and west sides of the device (middle right and middle left). The simplified CCCs without PLLs are located in the four corners of the device (Figure 4-16).







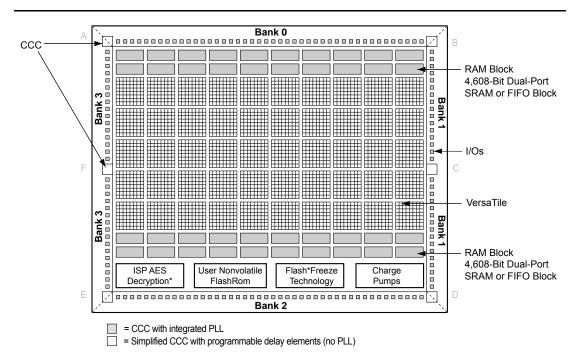


Figure 4-16 • CCC Locations in ProASIC3E Family Devices (PQFP-208 package)

256×18 FIFO is full, even though a 128×18 FIFO was requested. For this example, the Almost-Full flag can be used instead of the Full flag to signal when the 128th data word is reached.

To accommodate different aspect ratios, the almost-full and almost-empty values are expressed in terms of data bits instead of data words. SmartGen translates the user's input, expressed in data words, into data bits internally. SmartGen allows the user to select the thresholds for the Almost-Empty and Almost-Full flags in terms of either the read data words or the write data words, and makes the appropriate conversions for each flag.

After the empty or full states are reached, the FIFO can be configured so the FIFO counters either stop or continue counting. For timing numbers, refer to the appropriate family datasheet.

Signal Descriptions for FIFO4K18

The following signals are used to configure the FIFO4K18 memory element:

WW and RW

These signals enable the FIFO to be configured in one of the five allowable aspect ratios (Table 6-6).

WW[2:0]	RW[2:0]	D×W
000	000	4k×1
001	001	2k×2
010	010	1k×4
011	011	512×9
100	100	256×18
101, 110, 111	101, 110, 111	Reserved

Table 6-6 • Aspect Ratio Settings for WW[2:0]

WBLK and RBLK

These signals are active-low and will enable the respective ports when LOW. When the RBLK signal is HIGH, that port's outputs hold the previous value.

WEN and REN

Read and write enables. WEN is active-low and REN is active-high by default. These signals can be configured as active-high or -low.

WCLK and RCLK

These are the clock signals for the synchronous read and write operations. These can be driven independently or with the same driver.

Note: For the Automotive ProASIC3 FIFO4K18, for the same clock, 180° out of phase (inverted) between clock pins should be used.

RPIPE

This signal is used to specify pipelined read on the output. A LOW on RPIPE indicates a nonpipelined read, and the data appears on the output in the same clock cycle. A HIGH indicates a pipelined read, and data appears on the output in the next clock cycle.

RESET

This active-low signal resets the control logic and forces the output hold state registers to zero when asserted. It does not reset the contents of the memory array (Table 6-7 on page 160).

While the RESET signal is active, read and write operations are disabled. As with any asynchronous RESET signal, care must be taken not to assert it too close to the edges of active read and write clocks.

WD

This is the input data bus and is 18 bits wide. Not all 18 bits are valid in all configurations. When a data width less than 18 is specified, unused higher-order signals must be grounded (Table 6-7 on page 160).

The ROM emulation application is based on RAM block initialization. If the user's main design has access only to the read ports of the RAM block (RADDR, RD, RCLK, and REN), and the contents of the RAM are already initialized through the TAP, then the memory blocks will emulate ROM functionality for the core design. In this case, the write ports of the RAM blocks are accessed only by the user interface block, and the interface is activated only by the TAP Instruction Register contents.

Users should note that the contents of the RAM blocks are lost in the absence of applied power. However, the 1 kbit of flash memory, FlashROM, in low power flash devices can be used to retain data after power is removed from the device. Refer to the "SRAM and FIFO Memories in Microsemi's Low Power Flash Devices" section on page 147 for more information.

Sample Verilog Code

Interface Block

```
`define Initialize_start 8'h22 //INITIALIZATION START COMMAND VALUE
`define Initialize_stop 8'h23 //INITIALIZATION START COMMAND VALUE
module interface(IR, rst_n, data_shift, clk_in, data_update, din_ser, dout_ser, test,
  test_out,test_clk,clk_out,wr_en,rd_en,write_word,read_word,rd_addr, wr_addr);
input [7:0] IR;
input [3:0] read_word; //RAM DATA READ BACK
input rst_n, data_shift, clk_in, data_update, din_ser; //INITIALIZATION SIGNALS
input test, test_clk; //TEST PROCEDURE CLOCK AND COMMAND INPUT
output [3:0] test_out; //READ DATA
output [3:0] write_word; //WRITE DATA
output [1:0] rd_addr; //READ ADDRESS
output [1:0] wr_addr; //WRITE ADDRESS
output dout_ser; //TDO DRIVER
output clk_out, wr_en, rd_en;
wire [3:0] write_word;
wire [1:0] rd addr;
wire [1:0] wr_addr;
wire [3:0] Q_out;
wire enable, test_active;
reg clk out;
//SELECT CLOCK FOR INITIALIZATION OR READBACK TEST
always @(enable or test_clk or data_update)
begin
  case ({test_active})
    1 : clk_out = test_clk ;
    0 : clk_out = !data_update;
    default : clk_out = 1'b1;
  endcase
end
assign test_active = test && (IR == 8'h23);
assign enable = (IR == 8'h22);
assign wr_en = !enable;
assign rd_en = !test_active;
assign test_out = read_word;
assign dout_ser = Q_out[3];
//4-bit SIN/POUT SHIFT REGISTER
shift_reg data_shift_reg (.Shiften(data_shift), .Shiftin(din_ser), .Clock(clk_in),
  .Q(Q_out));
//4-bit PIPELINE REGISTER
D_pipeline pipeline_reg (.Data(Q_out), .Clock(data_update), .Q(write_word));
```

Microsemi

SRAM and FIFO Memories in Microsemi's Low Power Flash Devices

Date	Changes	Page
v1.1 (continued)	Table 6-1 • Flash-Based FPGAs and associated text were updated to include the IGLOO PLUS family. The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	150
	The text introducing Table 6-8 • Memory Availability per IGLOO and ProASIC3 Device was updated to replace "A3P030 and AGL030" with "15 k and 30 k gate devices." Table 6-8 • Memory Availability per IGLOO and ProASIC3 Device was updated to remove AGL400 and AGLE1500 and include IGLOO PLUS and ProASIC3L devices.	162



I/O Structures in IGLOO and ProASIC3 Devices

Solution 3

The board-level design must ensure that the reflected waveform at the pad does not exceed the voltage overshoot/undershoot limits provided in the datasheet. This is a requirement to ensure long-term reliability.

This scheme will also work for a 3.3 V PCI/PCI-X configuration, but the internal diode should not be used for clamping, and the voltage must be limited by the bus switch, as shown in Figure 7-11. Relying on the diode clamping would create an excessive pad DC voltage of 3.3 V + 0.7 V = 4 V.

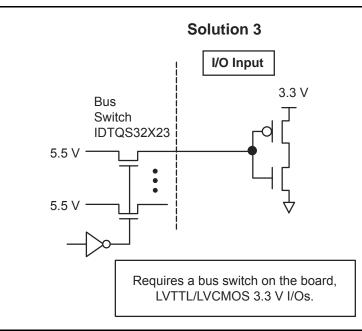


Figure 7-11 • Solution 3

Solution 4

The board-level design must ensure that the reflected waveform at the pad does not exceed the voltage overshoot/undershoot limits provided in the datasheet. This is a requirement to ensure long-term reliability.

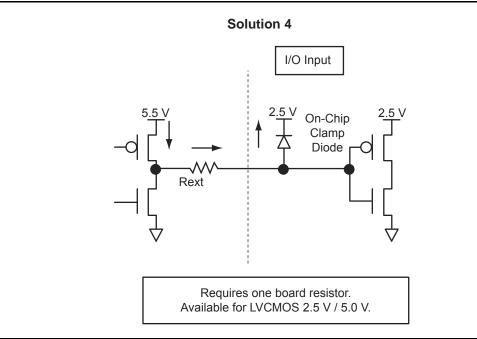


Figure 7-12 • Solution 4

Power-Up Behavior

Low power flash devices are power-up/-down friendly; i.e., no particular sequencing is required for power-up and power-down. This eliminates extra board components for power-up sequencing, such as a power-up sequencer.

During power-up, all I/Os are tristated, irrespective of I/O macro type (input buffers, output buffers, I/O buffers with weak pull-ups or weak pull-downs, etc.). Once I/Os become activated, they are set to the user-selected I/O macros. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 373 for details.

Drive Strength

Low power flash devices have up to seven programmable output drive strengths. The user can select the drive strength of a particular output in the I/O Attribute Editor or can instantiate a specialized I/O macro, such as OUTBUF_S_12 (slew = low, out_drive = 12 mA).

The maximum available drive strength is 24 mA per I/O. Though no I/O should be forced to source or sink more than 24 mA indefinitely, I/Os may handle a higher amount of current (refer to the device IBIS model for maximum source/sink current) during signal transition (AC current). Every device package has its own power dissipation limit; hence, power calculation must be performed accurately to determine how much current can be tolerated per I/O within that limit.

I/O Interfacing

Low power flash devices are 5 V–input– and 5 V–output–tolerant if certain I/O standards are selected (refer to the "5 V Input and Output Tolerance" section on page 232). Along with other low-voltage I/O macros, this 5 V tolerance makes these devices suitable for many types of board component interfacing.

Table 8-19 shows some hi	gh-level interfacing	examples using	low power flash devices.

	(Clock	I/O			
Interface	Туре	Frequency	Туре	Signals In	Signals Out	Data I/O
GM	Src Sync	125 MHz	LVTTL	8	8	125 Mbps
ТВІ	Src Sync	125 MHz	LVTTL	10	10	125 Mbps
XSBI	Src Sync	644 MHz	LVDS	16	16	644 Mbps
XGMI	Src Sync DDR	156 MHz	HSTL1	32	32	312 Mbps
FlexBus 3	Sys Sync	104 MHz	LVTTL	≤ 32	≤ 32	≤ 104
Pos-PHY3/SPI-3	Sys Sync	104	LVTTL	8,16,32	8,16,32	\leq 104 Mbps
FlexBus 4/SPI-4.1	Src Sync	200 MHz	HSTL1	16,64	16,64	200 Mbps
Pos-PHY4/SPI-4.2	Src Sync DDR	≥ 311 MHz	LVDS	16	16	\geq 622 Mbps
SFI-4.1	Src Sync	622 MHz	LVDS	16	16	622 Mbps
CSIX L1	Sys Sync	\leq 250 MHz	HSTL1	32,64,96,128	32,64,96,128	\leq 250 Mbps
Hyper Transport	Sys Sync DDR	\leq 800 MHz	LVDS	2,4,8,16	2,4,8,16	\leq 1.6 Gbps
Rapid I/O Parallel	Sys Sync DDR	250 MHz – 1 GHz	LVDS	8,16	8,16	≤ 2 Gbps
Star Fabric	CDR		LVDS	4	4	622 Mbps

Table 8-19 • High-Level Interface Examples

Note: Sys Sync = System Synchronous Clocking, Src Sync = Source Synchronous Clocking, and CDR = Clock and Data Recovery.

General Flash Programming Information

Programming Basics

When choosing a programming solution, there are a number of options available. This section provides a brief overview of those options. The next sections provide more detail on those options as they apply to Microsemi FPGAs.

Reprogrammable or One-Time-Programmable (OTP)

Depending on the technology chosen, devices may be reprogrammable or one-time-programmable. As the name implies, a reprogrammable device can be programmed many times. Generally, the contents of such a device will be completely overwritten when it is reprogrammed. All Microsemi flash devices are reprogrammable.

An OTP device is programmable one time only. Once programmed, no more changes can be made to the contents. Microsemi flash devices provide the option of disabling the reprogrammability for security purposes. This combines the convenience of reprogrammability during design verification with the security of an OTP technology for highly sensitive designs.

Device Programmer or In-System Programming

There are two fundamental ways to program an FPGA: using a device programmer or, if the technology permits, using in-system programming. A device programmer is a piece of equipment in a lab or on the production floor that is used for programming FPGA devices. The devices are placed into a socket mounted in a programming adapter module, and the appropriate electrical interface is applied. The programmed device can then be placed on the board. A typical programmer, used during development, programs a single device at a time and is referred to as a single-site engineering programmer.

With ISP, the device is already mounted onto the system printed circuit board when programming occurs. Typically, ISD programming is performed via a JTAG interface on the FPGA. The JTAG pins can be controlled either by an on-board resource, such as a microprocessor, or by an off-board programmer through a header connection. Once mounted, it can be programmed repeatedly and erased. If the application requires it, the system can be designed to reprogram itself using a microprocessor, without the use of any external programmer.

If multiple devices need to be programmed with the same program, various multi-site programming hardware is available in order to program many devices in parallel. Microsemi In House Programming is also available for this purpose.

Programming Features for Microsemi Devices

Flash Devices

The flash devices supplied by Microsemi are reprogrammable by either a generic device programmer or ISP. Microsemi supports ISP using JTAG, which is supported by the FlashPro4 and FlashPro3, FlashPro Lite, Silicon Sculptor 3, and Silicon Sculptor II programmers.

Levels of ISP support vary depending on the device chosen:

- All SmartFusion, Fusion, IGLOO, and ProASIC3 devices support ISP.
- IGLOO, IGLOOe, IGLOO nano V5, and IGLOO PLUS devices can be programmed in-system when the device is using a 1.5 V supply voltage to the FPGA core.
- IGLOO nano V2 devices can be programmed at 1.2 V core voltage (when using FlashPro4 only) or 1.5 V. IGLOO nano V5 devices are programmed with a VCC core voltage of 1.5 V.



Programming Flash Devices

Signal Integrity While Using ISP

For ISP of flash devices, customers are expected to follow the board-level guidelines provided on the Microsemi SoC Products Group website. These guidelines are discussed in the datasheets and application notes (refer to the "Related Documents" section of the datasheet for application note links). Customers are also expected to troubleshoot board-level signal integrity issues by measuring voltages and taking oscilloscope plots.

Programming Failure Allowances

Microsemi has strict policies regarding programming failure allowances. Please refer to *Programming and Functional Failure Guidelines* on the Microsemi SoC Products Group website for details.

Contacting the Customer Support Group

Highly skilled engineers staff the Customer Applications Center from 7:00 A.M. to 6:00 P.M., Pacific time, Monday through Friday. You can contact the center by one of the following methods:

Electronic Mail

You can communicate your technical questions to our email address and receive answers back by email, fax, or phone. Also, if you have design problems, you can email your design files to receive assistance. Microsemi monitors the email account throughout the day. When sending your request to us, please be sure to include your full name, company name, and contact information for efficient processing of your request. The technical support email address is soc_tech@microsemi.com.

Telephone

Our Technical Support Hotline answers all calls. The center retrieves information, such as your name, company name, telephone number, and question. Once this is done, a case number is assigned. Then the center forwards the information to a queue where the first available applications engineer receives the data and returns your call. The phone hours are from 7:00 A.M. to 6:00 P.M., Pacific time, Monday through Friday.

The Customer Applications Center number is (800) 262-1060.

European customers can call +44 (0) 1256 305 600.



Security in Low Power Flash Devices

The AES key is securely stored on-chip in dedicated low power flash device flash memory and cannot be read out. In the first step, the AES key is generated and programmed into the device (for example, at a secure or trusted programming site). The Microsemi Designer software tool provides AES key generation capability. After the key has been programmed into the device, the device will only correctly decrypt programming files that have been encrypted with the same key. If the individual programming file content is incorrect, a Message Authentication Control (MAC) mechanism inside the device will fail in authenticating the programming file. In other words, when an encrypted programming file is being loaded into a device that has a different programmed AES key, the MAC will prevent this incorrect data from being loaded, preventing possible device damage. See Figure 12-3 on page 304 and Figure 12-4 on page 306 for graphical representations of this process.

It is important to note that the user decides what level of protection will be implemented for the device. When AES protection is desired, the FlashLock Pass Key must be set. The AES key is a content protection mechanism, whereas the FlashLock Pass Key is a device protection mechanism. When the AES key is programmed into the device, the device still needs the Pass Key to protect the FPGA and FlashROM contents and the security settings, including the AES key. Using the FlashLock Pass Key prevents modification of the design contents by means of simply programming the device with a different AES key.

AES Decryption and MAC Authentication

Low power flash devices have a built-in 128-bit AES decryption core, which decrypts the encrypted programming file and performs a MAC check that authenticates the file prior to programming.

MAC authenticates the entire programming data stream. After AES decryption, the MAC checks the data to make sure it is valid programming data for the device. This can be done while the device is still operating. If the MAC validates the file, the device will be erased and programmed. If the MAC fails to validate, then the device will continue to operate uninterrupted.

This will ensure the following:

- · Correct decryption of the encrypted programming file
- Prevention of erroneous or corrupted data being programmed during the programming file transfer
- Correct bitstream passed to the device for decryption

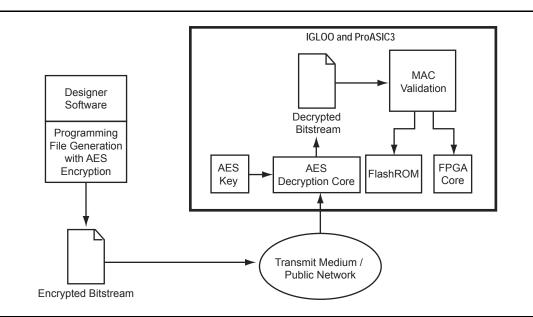


Figure 12-4 • Example Application Scenario Using AES in IGLOO and ProASIC3 Devices

1. National Institute of Standards and Technology, "ADVANCED ENCRYPTION STANDARD (AES) Questions and Answers," 28 January 2002 (10 January 2005). See http://csrc.nist.gov/archive/aes/index1.html for more information.

List of Changes

Date	Changes	Page
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
v1.1 (October 2008)	The "Introduction" was revised to include information about the core supply voltage range of operation in V2 devices.	341
	IGLOO nano device support was added to Table 14-1 • Flash-Based FPGAs Supporting Voltage Switching Circuit.	342
	The "Circuit Description" section was updated to include IGLOO PLUS core operation from 1.2 V to 1.5 V in 50 mV increments.	343
v1.0 (August 2008)	The "Microsemi's Flash Families Support Voltage Switching Circuit" section was revised to include new families and make the information more concise.	342

The following table lists critical changes that were made in each revision of the chapter.

16 – Boundary Scan in Low Power Flash Devices

Boundary Scan

Low power flash devices are compatible with IEEE Standard 1149.1, which defines a hardware architecture and the set of mechanisms for boundary scan testing. JTAG operations are used during boundary scan testing.

The basic boundary scan logic circuit is composed of the TAP controller, test data registers, and instruction register (Figure 16-2 on page 360).

Low power flash devices support three types of test data registers: bypass, device identification, and boundary scan. The bypass register is selected when no other register needs to be accessed in a device. This speeds up test data transfer to other devices in a test data path. The 32-bit device identification register is a shift register with four fields (LSB, ID number, part number, and version). The boundary scan register observes and controls the state of each I/O pin. Each I/O cell has three boundary scan register cells, each with serial-in, serial-out, parallel-in, and parallel-out pins.

TAP Controller State Machine

The TAP controller is a 4-bit state machine (16 states) that operates as shown in Figure 16-1.

The 1s and 0s represent the values that must be present on TMS at a rising edge of TCK for the given state transition to occur. IR and DR indicate that the instruction register or the data register is operating in that state.

The TAP controller receives two control inputs (TMS and TCK) and generates control and clock signals for the rest of the test logic architecture. On power-up, the TAP controller enters the Test-Logic-Reset state. To guarantee a reset of the controller from any of the possible states, TMS must remain HIGH for five TCK cycles. The TRST pin can also be used to asynchronously place the TAP controller in the Test-Logic-Reset state.

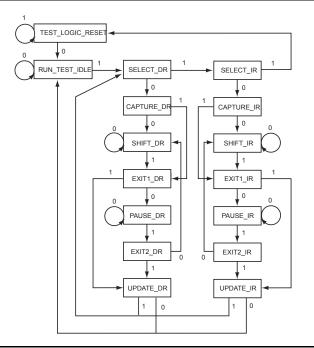


Figure 16-1 • TAP Controller State Machine

Brownout Voltage

Brownout is a condition in which the voltage supplies are lower than normal, causing the device to malfunction as a result of insufficient power. In general, Microsemi does not guarantee the functionality of the design inside the flash FPGA if voltage supplies are below their minimum recommended operating condition. Microsemi has performed measurements to characterize the brownout levels of FPGA power supplies. Refer to Table 18-3 for device-specific brownout deactivation levels. For the purpose of characterization, a direct path from the device input to output is monitored while voltage supplies are lowered gradually. The brownout point is defined as the voltage level at which the output stops following the input. Characterization tests performed on several IGLOO, ProASIC3L, and ProASIC3 devices in typical operating conditions showed the brownout voltage levels to be within the specification.

During device power-down, the device I/Os become tristated once the first supply in the power-down sequence drops below its brownout deactivation voltage.

Table 18-3 • Brownout Deactivation Levels for VCC and VCCI

Devices	VCC Brownout Deactivation Level (V)	VCCI Brownout Deactivation Level (V)
ProASIC3, ProASIC3 nano, IGLOO, IGLOO nano, IGLOO PLUS and ProASIC3L devices running at VCC = 1.5 V	0.75 V ± 0.25 V	0.8 V ± 0.3 V
IGLOO, IGLOO nano, IGLOO PLUS, and ProASIC3L devices running at VCC = 1.2 V	0.75 V ± 0.2 V	0.8 V ± 0.15 V

PLL Behavior at Brownout Condition

When PLL power supply voltage and/or V_{CC} levels drop below the V_{CC} brownout levels mentioned above for 1.5 V and 1.2 V devices, the PLL output lock signal goes LOW and/or the output clock is lost. The following sections explain PLL behavior during and after the brownout condition.

VCCPLL and VCC Tied Together

In this condition, both VCC and VCCPLL drop below the 0.75 V (\pm 0.25 V or \pm 0.2 V) brownout level. During the brownout recovery, once VCCPLL and VCC reach the activation point (0.85 \pm 0.25 V or \pm 0.2 V) again, the PLL output lock signal may still remain LOW with the PLL output clock signal toggling. If this condition occurs, there are two ways to recover the PLL output lock signal:

- 1. Cycle the power supplies of the PLL (power off and on) by using the PLL POWERDOWN signal.
- 2. Turn off the input reference clock to the PLL and then turn it back on.

Only VCCPLL Is at Brownout

In this case, only VCCPLL drops below the 0.75 V (\pm 0.25 V or \pm 0.2 V) brownout level and the VCC supply remains at nominal recommended operating voltage (1.5 V \pm 0.075 V for 1.5 V devices and 1.2 V \pm 0.06 V for 1.2 V devices). In this condition, the PLL behavior after brownout recovery is similar to initial power-up condition, and the PLL will regain lock automatically after VCCPLL is ramped up above the activation level (0.85 \pm 0.25 V or \pm 0.2 V). No intervention is necessary in this case.

Only VCC Is at Brownout

In this condition, VCC drops below the 0.75 V (\pm 0.25 V or \pm 0.2 V) brownout level and VCCPLL remains at nominal recommended operating voltage (1.5 V \pm 0.075 V for 1.5 V devices and 1.2 V \pm 0.06 V for 1.2 V devices). During the brownout recovery, once VCC reaches the activation point again (0.85 \pm 0.25 V or \pm 0.2 V), the PLL output lock signal may still remain LOW with the PLL output clock signal toggling. If this condition occurs, there are two ways to recover the PLL output lock signal:

- 1. Cycle the power supplies of the PLL (power off and on) by using the PLL POWERDOWN signal.
- 2. Turn off the input reference clock to the PLL and then turn it back on.

It is important to note that Microsemi recommends using a monotonic power supply or voltage regulator to ensure proper power-up behavior.



Summary of Changes

Revision (month/year)	Chapter Affected	List of Changes (page number)
Revision 0	"DDR for Microsemi's Low Power Flash Devices" was revised.	285
(continued)	"Programming Flash Devices" was revised.	298
"In-System Programming (ISP) of Microsemi's Low Power Flash Do FlashPro4/3/3X" was revised.		339
	"Core Voltage Switching Circuit for IGLOO and ProASIC3L In-System Programming" was revised.	347
	"Boundary Scan in Low Power Flash Devices" was revised.	362